

Patent Claims

1. Substrate coating comprising a transparent Si_3N_4 or SiN_x layer (3) directly on a substrate (2), a semimetallic layer (4) above the Si_3N_4 or SiN_x layer (3) and with a further Si_3N_4 or SiN_x layer (6) as well as with a dielectric oxide layer (5) from the group Al_2O_3 , SnO , TiO_2 and SiO_2 , **characterized in** that the dielectric oxide layer (5) is disposed on the semimetallic layer (4) and the further Si_3N_4 layer (6) on the dielectric oxide layer (5).
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2. Substrate coating as claimed in claim 1, **characterized in** that the semimetallic layer is a CrN layer.
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3. Substrate coating as claimed in claim 1, **characterized in** that between the transparent Si_3N_4 or SiN_x layer (3) directly on the substrate (2) and the semimetallic layer (4) a dielectric oxide layer (10) is provided.
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4. Substrate coating as claimed in claim 1 or claim 3, **characterized in** that for the substoichiometric SiN_x layer, x is a number smaller than 4/3.
5. Substrate coating as claimed in claim 2, **characterized in** that, instead of the semimetallic CrN layer (4), a semimetallic NiCrN or NiCrO_x layer is provided.
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6. Substrate coating as claimed in one or several of the preceding claims, **characterized in** that the transparent Si_3N_4 or substoichiometric SiN_x layers (3, 6) have each a layer thickness of 20 to 120 nm.
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7. Substrate coating as claimed in one or several of the preceding claims, **characterized in** that the dielectric oxide layers (5, 10) have each a layer thickness of 4 to 120 nm.
8. Substrate coating as claimed in one or several of the preceding claims, **characterized in** that the semimetallic NiCrN, CrN (4) or NiCrO_x layers have a layer thickness of 5 to 40 nm.
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9. Substrate coating as claimed in claim 1, **characterized in** that the substrate (2) is glass.
10. Substrate coating as claimed in claim 1, **characterized in** that the substrate (2) is a synthetic material.
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11. Substrate coating as claimed in claim 1, **characterized in** that additional layers comprised of Cr, Ni or NiCr are provided.

12. Substrate coating as claimed in claim 1, **characterized in** that the dielectric oxide layer is comprised of Nb_2O_5 .